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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD
SEMICONDUCTOR®

October 2013

FDP2572

N-Channel PowerTrench® MOSFET
150 V, 29 A, 54 mΩ

Features

- $R_{DS(on)}$ = 45 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 9 A
- $Q_{G(tot)}$ = 26 nC (Typ.) @ V_{GS} = 10 V
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)

Formerly developmental type 82860

Applications

- Consumer Appliances
- Synchronous Rectification
- Battery Protection Circuit
- Motor drives and Uninterruptible Power Supplies
- Micro Solar Inverter

TO-220
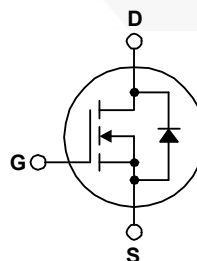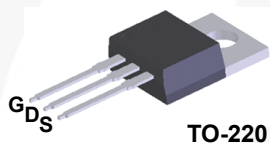
MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FDP2572	Unit
V_{DSS}	Drain to Source Voltage	150	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current		
	Continuous (T_C = 25°C, V_{GS} = 10V)	29	A
	Continuous (T_C = 100°C, V_{GS} = 10V)	20	A
	Continuous (T_{amb} = 25°C, V_{GS} = 10V, $R_{\theta JA}$ = 43°C/W)	4	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	36	mJ
P_D	Power dissipation	135	W
	Derate above 25°C	0.9	W/°C
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.11	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. (Note 2)	62.5	°C/W

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Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP2572	FDP2572	TO-220	Tube	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
Off Characteristics							
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = 250µA, V_{GS} = 0V		150	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120V		-	-	1	µA
		V_{GS} = 0V	T_C = 150°	-	-	250	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V		-	-	±100	nA
On Characteristics							
$V_{GS(TH)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250µA		2	-	4	V
$r_{DS(ON)}$	Drain to Source On Resistance	I_D = 9A, V_{GS} = 10V		-	0.045	0.054	Ω
		I_D = 4A, V_{GS} = 6V,		-	0.050	0.075	
		I_D=9A, V_{GS}=10V, T_C=175°C		-	0.126	0.146	
Dynamic Characteristics							
C_{ISS}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz		-	1770	-	pF
C_{OSS}	Output Capacitance			-	183	-	pF
C_{RSS}	Reverse Transfer Capacitance			-	40	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{GS} = 0V to 10V	V_{DD} = 75V I_D = 9A I_g = 1.0mA	-	26	34	nC
$Q_{g(TH)}$	Threshold Gate Charge	V_{GS} = 0V to 2V		-	3.3	4.3	nC
Q_{gs}	Gate to Source Gate Charge			-	8	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau			-	5	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	6	-	nC
Resistive Switching Characteristics (V_{GS} = 10V)							
t_{ON}	Turn-On Time	V_{DD} = 75V, I_D = 9A V_{GS} = 10V, R_{GS} = 11.0Ω		-	-	36	ns
$t_{d(ON)}$	Turn-On Delay Time			-	11	-	ns
t_r	Rise Time			-	14	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time			-	31	-	ns
t_f	Fall Time			-	14	-	ns
t_{OFF}	Turn-Off Time			-	-	66	ns
Drain-Source Diode Characteristics							
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 9A		-	-	1.25	V
		I_{SD} = 4A		-	-	1.0	V
t_{rr}	Reverse Recovery Time	I_{SD} = 9A, dI_{SD}/dt =100A/µs		-	-	74	ns
Q_{RR}	Reverse Recovered Charge	I_{SD} = 9A, dI_{SD}/dt =100A/µs		-	-	169	nC

Notes:
1: Starting T_J = 25°C, L = 0.2mH, I_{AS} = 19A.
2: Pulse Width = 100s

Typical Characteristics T_C = 25°C unless otherwise noted

POWER DISSIPATION MULTIPLIER

T_C, CASE TEMPERATURE (°C)
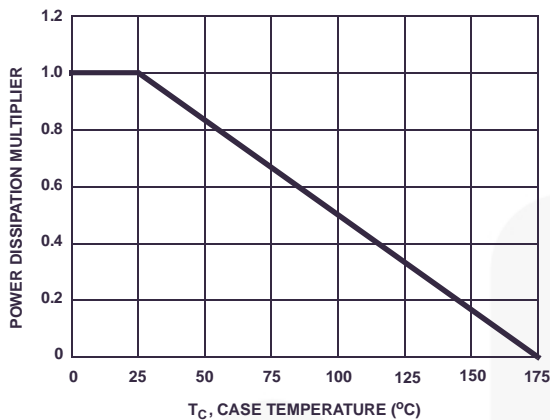
Figure 1. Normalized Power Dissipation vs Ambient Temperature

V_{GS} = 10V

I_D, DRAIN CURRENT (A)

T_C, CASE TEMPERATURE (°C)
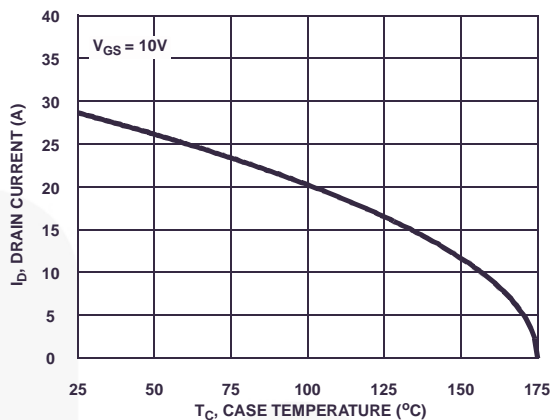
Figure 2. Maximum Continuous Drain Current vs Case Temperature

$Z_{\theta JC}$, NORMALIZED THERMAL IMPEDANCE

DUTY CYCLE - DESCENDING ORDER
0.5
0.2
0.1
0.05
0.02
0.01

SINGLE PULSE

P_{DM}

t_1

t_2

NOTES:
DUTY FACTOR: D = t_1/t_2
PEAK T_J = P_{DM} x $Z_{\theta JC}$ x $R_{\theta JC}$ + T_C

t, RECTANGULAR PULSE DURATION (s)
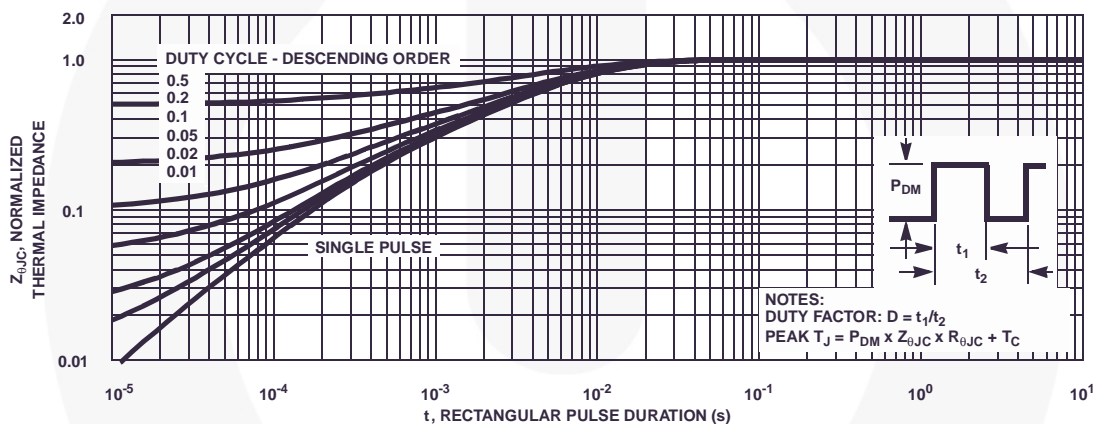
Figure 3. Normalized Maximum Transient Thermal Impedance

I_{DM}, PEAK CURRENT (A)

TRANSCONDUCTANCE MAY LIMIT CURRENT IN THIS REGION

T_C = 25°C
FOR TEMPERATURES ABOVE 25°C DERATE PEAK CURRENT AS FOLLOWS:

$I = I_{25} \sqrt{\dfrac{175 - T_C}{150}}$

V_{GS} = 10V

t, PULSE WIDTH (s)
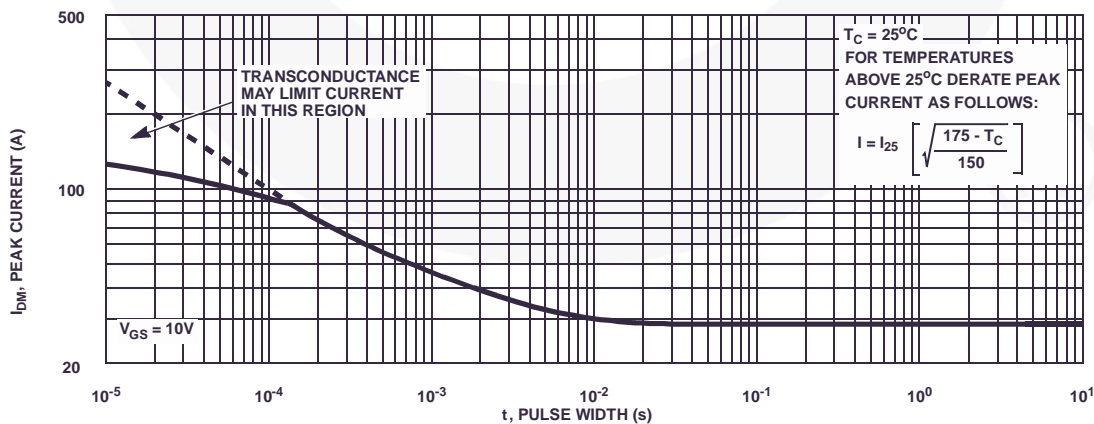
Figure 4. Peak Current Capability

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Typical Characteristics T_C = 25°C unless otherwise noted
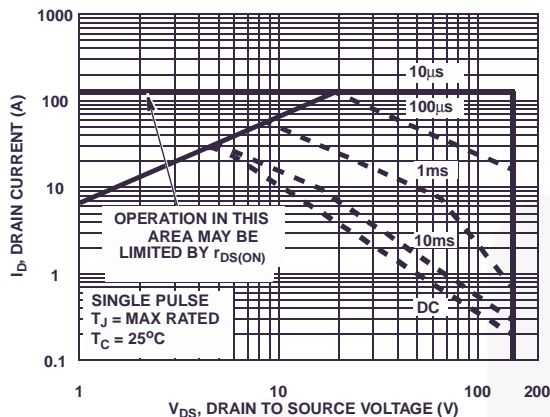
Figure 5. Forward Bias Safe Operating Area

NOTE: Refer to Fairchild Application Notes AN7514 and AN7515
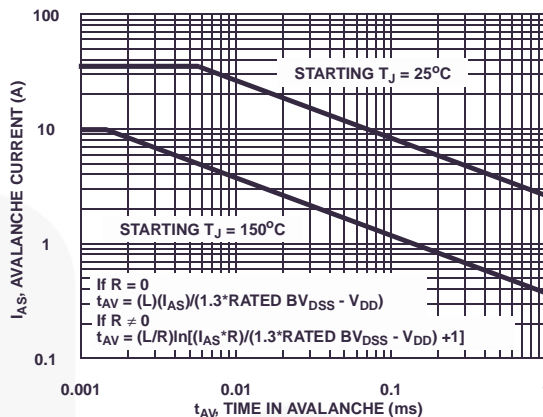
Figure 6. Unclamped Inductive Switching Capability

$$\text{If } R = 0$$
$$t_{AV} = (L)(I_{AS})/(1.3*\text{RATED } BV_{DSS} - V_{DD})$$
$$\text{If } R \neq 0$$
$$t_{AV} = (L/R)\ln[(I_{AS}*R)/(1.3*\text{RATED } BV_{DSS} - V_{DD}) +1]$$

Figure 7. Transfer Characteristics
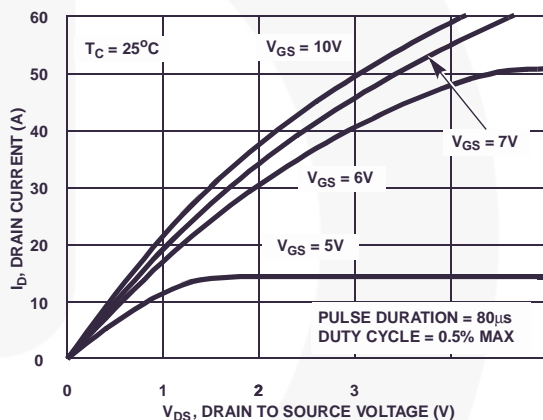
Figure 8. Saturation Characteristics
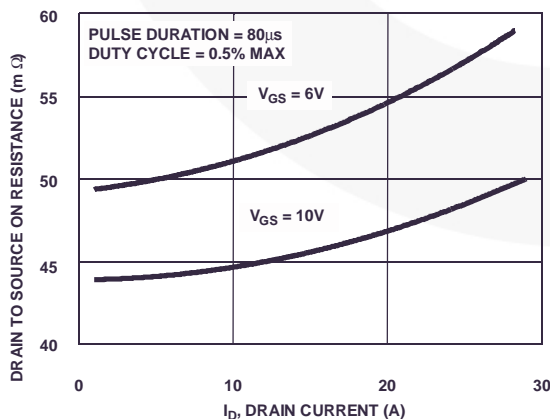
Figure 9. Drain to Source On Resistance vs Drain Current
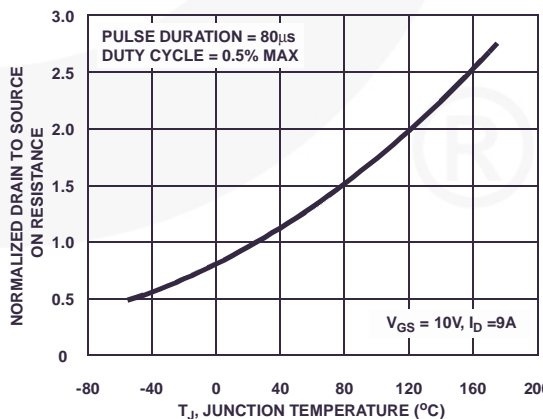
Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

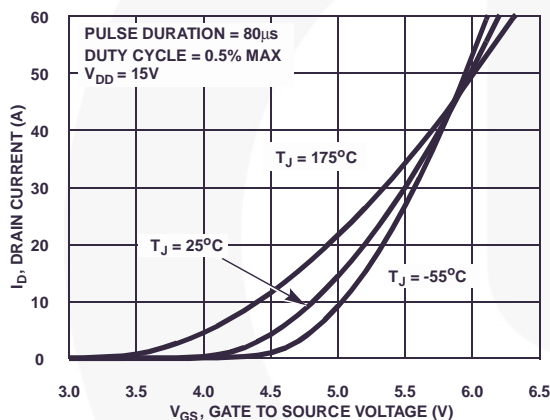## Typical Characteristics T_C = 25°C unless otherwise noted
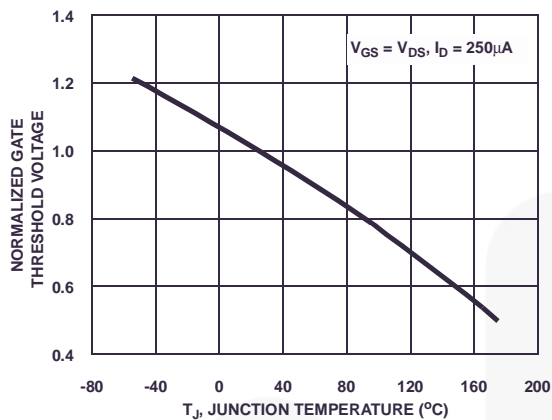
Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature
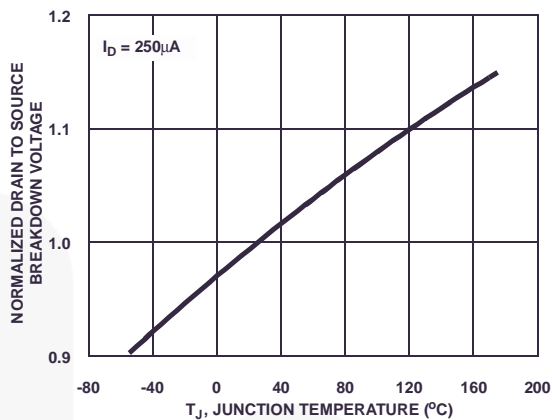
Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature
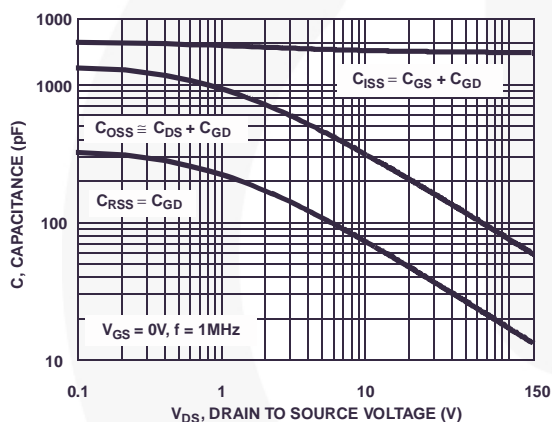
Figure 13. Capacitance vs Drain to Source Voltage
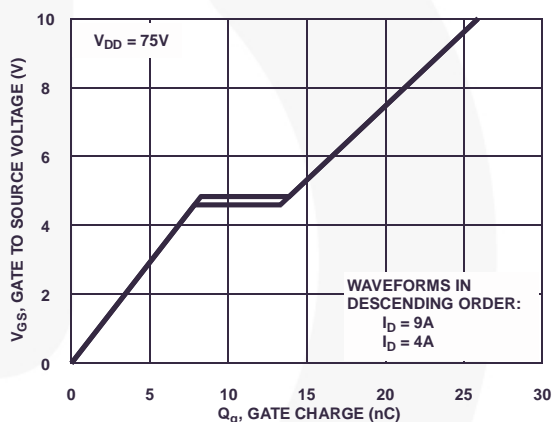
Figure 14. Gate Charge Waveforms for Constant Gate Currents

Test Circuits and Waveforms

FDP2572 — N-Channel PowerTrench® MOSFET

Figure 15. Unclamped Energy Test Circuit

Figure 16. Unclamped Energy Waveforms

Figure 17. Gate Charge Test Circuit

**Figure 18. Gate Charge Waveforms**

Figure 19. Switching Time Test Circuit

Figure 20. Switching Time Waveforms

FDP2572 Rev. C1

6

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
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PSPICE Electrical Model

```
.SUBCKT FDB2572 2 1 3 ;      rev April 2002
CA  12  8 5.5e-10
Cb 15 14 7.4e-10
Cin 6 8 1.7e-9

Dbody 7 5 DbodyMOD
Dbreak 5 11 DbreakMOD
Dplcap 10 5 DplcapMOD

Ebreak 11 7 17 18 160
Eds 14 8 5 8 1
Egs 13 8 6 8 1
Esg 6 10 6 8 1
Evthres 6 21 19 8 1
Evtemp 20 6 18 22 1

It 8 17 1

Lgate 1 9 9.56e-9
Ldrain 2 5 1.0e-9
Lsource 3 7 7.71e-9

RLgate 1 9 95.6
RLdrain 2 5 10
RLsource 3 7 77.1

Mmed 16 6 8 8 MmedMOD
Mstro 16 6 8 8 MstroMOD
Mweak 16 21 8 8 MweakMOD

Rbreak 17 18 RbreakMOD 1
Rdrain 50 16 RdrainMOD 35e-3
Rgate 9 20 1.6
RSLC1 5 51 RSLCMOD 1.0e-6
RSLC2 5 50 1.0e3
Rsource 8 7 RsourceMOD 3.0e-3
Rvthres 22 8 RvthresMOD 1
Rvtemp 18 19 RvtempMOD 1
S1a 6 12 13 8 S1AMOD
S1b 13 12 13 8 S1BMOD
S2a 6 15 14 13 S2AMOD
S2b 13 15 14 13 S2BMOD

Vbat 22 19 DC 1

ESLC 51 50  VALUE={(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*52),3))}

.MODEL DbodyMOD D (IS=6.0E-11 N=1.14 RS=3.9e-3 TRS1=3.5e-3 TRS2=3.0e-6
+ CJO=1.1e-9 M=0.63 TT=6.2e-8 XTI=4.5)
.MODEL DbreakMOD D (RS=10 TRS1=5.0e-3 TRS2=-5.0e-6)
.MODEL DplcapMOD D (CJO=3.5e-10 IS=1.0e-30 N=10 M=0.65)

.MODEL MmedMOD NMOS (VTO=3.55 KP=3 IS=1e-40 N=10 TOX=1 L=1u W=1u RG=1.6)
.MODEL MstroMOD NMOS (VTO=4.0 KP=25 IS=1e-30 N=10 TOX=1 L=1u W=1u)
.MODEL MweakMOD NMOS (VTO=2.95 KP=0.05 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=16 RS=0.1)

.MODEL RbreakMOD RES (TC1=1.15e-3 TC2=-9.5e-7)
.MODEL RdrainMOD RES (TC1=9.0e-3 TC2=2.5e-5)
.MODEL RSLCMOD RES (TC1=3.0e-3 TC2=2.5e-6)
.MODEL RsourceMOD RES (TC1=4.0e-3 TC2=1.0e-6)
.MODEL RvthresMOD RES (TC1=-4.1e-3 TC2=-1.0e-5)
.MODEL RvtempMOD RES (TC1=-4.0e-3 TC2=1.0e-6)

.MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-5.0 VOFF=-3.5)
.MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-3.5 VOFF=-5.0)
.MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-0.5 VOFF=0.3)
.MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=0.3 VOFF=-0.5)
.ENDS
```
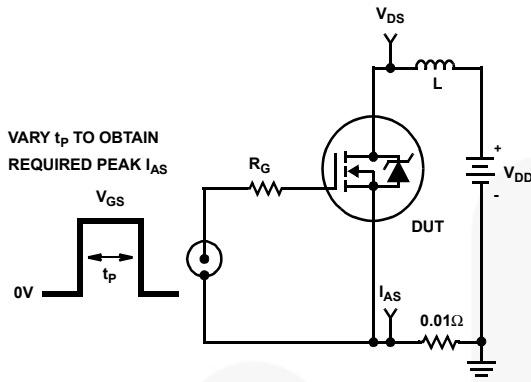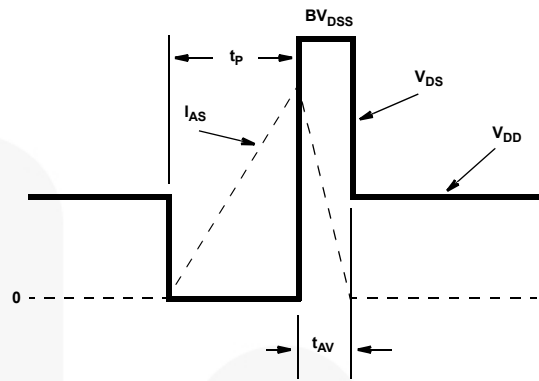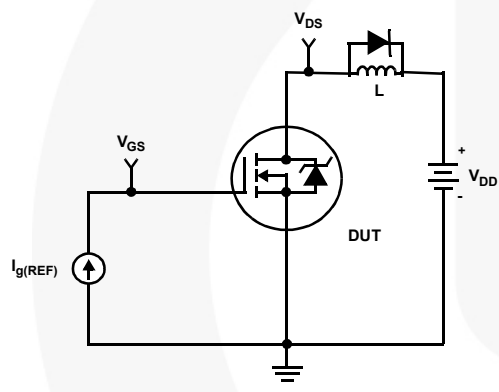
Note: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.
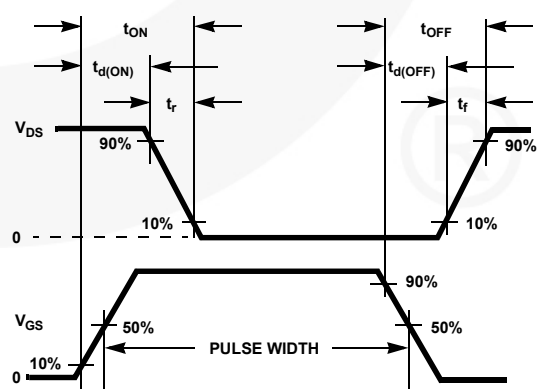
SABER Electrical Model

REV April 2002
ttemplate FDB2572 n2,n1,n3
electrical n2,n1,n3
{
var i iscl
dp..model dbodymod = (isl=6.0e-11,nl=1.14,rs=3.9e-3,trs1=3.5e-3,trs2=3.0e-6,cjo=1.1e-9,m=0.63,tt=6.2e-8,xti=4.5)
dp..model dbreakmod = (rs=10,trs1=5.0e-3,trs2=-5.0e-6)
dp..model dplcapmod = (cjo=3.5e-10,isl=10.0e-30,nl=10,m=0.65)
m..model mmedmod = (type=_n,vto=3.55,kp=3,is=1e-40, tox=1)
m..model mstrongmod = (type=_n,vto=4.0,kp=25,is=1e-30, tox=1)
m..model mweakmod = (type=_n,vto=2.95,kp=0.05,is=1e-30, tox=1,rs=0.1)
sw_vcsp..model s1amod = (ron=1e-5,roff=0.1,von=-5.0,voff=-3.5)
sw_vcsp..model s1bmod = (ron=1e-5,roff=0.1,von=-3.5,voff=-5.0)
sw_vcsp..model s2amod = (ron=1e-5,roff=0.1,von=-0.5,voff=0.3)
sw_vcsp..model s2bmod = (ron=1e-5,roff=0.1,von=0.3,voff=-0.5)
c.ca n12 n8 = 5.5e-10
c.cb n15 n14 = 7.4e-10
c.cin n6 n8 = 1.7e-9

dp.dbody n7 n5 = model=dbodymod
dp.dbreak n5 n11 = model=dbreakmod
dp.dplcap n10 n5 = model=dplcapmod

spe.ebreak n11 n7 n17 n18 = 160
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evthres n6 n21 n19 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1

i.it n8 n17 = 1

l.lgate n1 n9 = 9.56e-9
l.ldrain n2 n5 = 1.0e-9
l.lsource n3 n7 = 7.71e-9

res.rlgate n1 n9 = 95.6
res.rldrain n2 n5 = 10
res.rlsource n3 n7 = 77.1

m.mmed n16 n6 n8 n8 = model=mmedmod, l=1u, w=1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, l=1u, w=1u
m.mweak n16 n21 n8 n8 = model=mweakmod, l=1u, w=1u

res.rbreak n17 n18 = 1, tc1=1.15e-3,tc2=-9.5e-7
res.rdrain n50 n16 = 35e-3, tc1=9.0e-3,tc2=2.5e-5
res.rslc1 n5 n51 = 1.0e-6, tc1=3.0e-3,tc2=2.5e-6
res.rslc2 n5 n50 = 1.0e3
res.rsource n8 n7 = 3.0e-3, tc1=4.0e-3,tc2=1.0e-6
res.rvthres n22 n8 = 1, tc1=-4.1e-3,tc2=-1.0e-5
res.rvtemp n18 n19 = 1, tc1=-4.0e-3,tc2=1.0e-6
sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod

v.vbat n22 n19 = dc=1
equations {
i (n51->n50) +=iscl
iscl: v(n51,n50) = ((v(n5,n51)/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51)*1e6/52))** 3))}
}
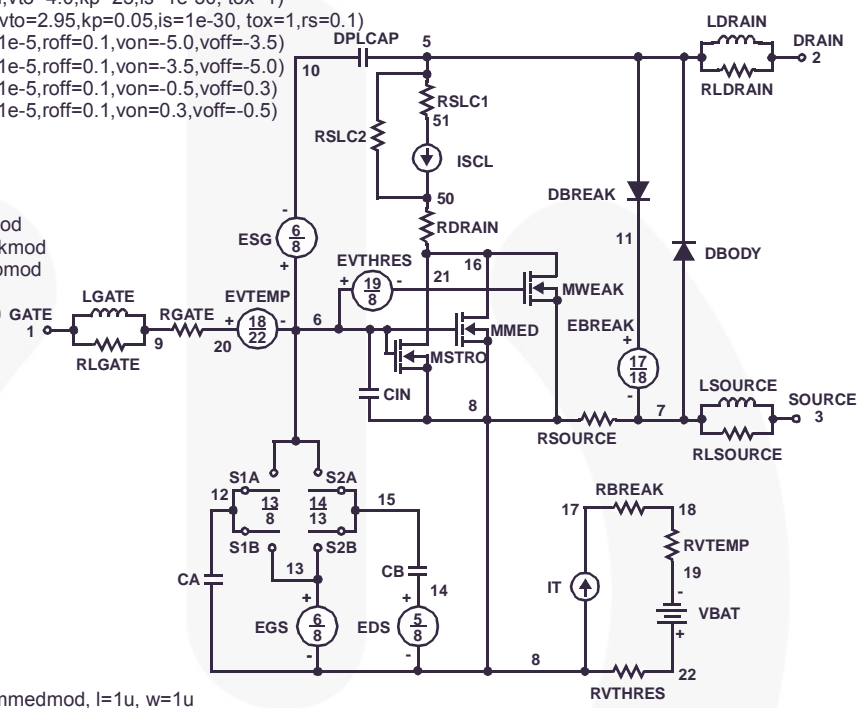
SPICE Thermal Model

REV 26 April 2002

FDB2572

CTHERM1 TH 6 3.8e-3
CTHERM2 6 5 4.0e-3
CTHERM3 5 4 4.2e-3
CTHERM4 4 3 4.3e-3
CTHERM5 3 2 8.5e-3
CTHERM6 2 TL 3.0e-2

RTHERM1 TH 6 5.5e-4
RTHERM2 6 5 5.0e-3
RTHERM3 5 4 4.5e-2
RTHERM4 4 3 10.5e-2
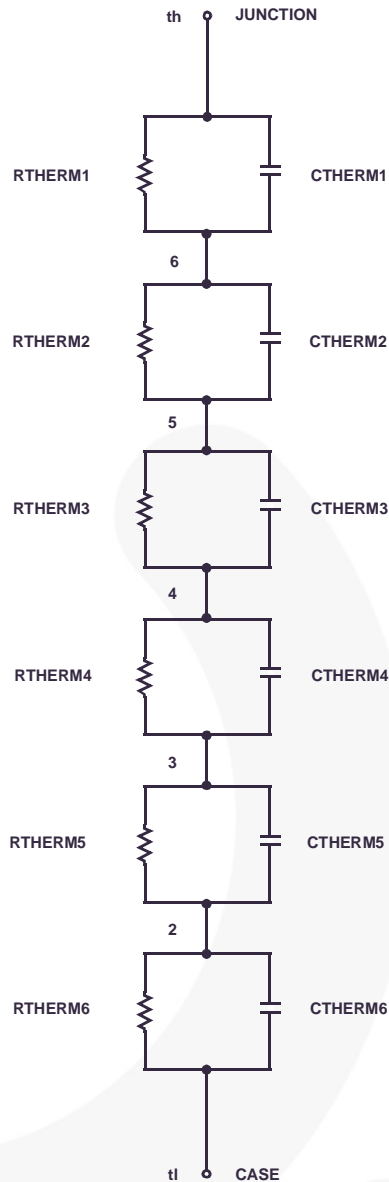RTHERM5 3 2 3.7e-1
RTHERM6 2 TL 3.8e-1

SABER Thermal Model

SABER thermal model FDB2572
template thermal_model th tl
thermal_c th, tl
{
ctherm.ctherm1 th 6 =3.8e-3
ctherm.ctherm2 6 5 =4.0e-3
ctherm.ctherm3 5 4 =4.2e-3
ctherm.ctherm4 4 3 =4.3e-3
ctherm.ctherm5 3 2 =8.5e-3
ctherm.ctherm6 2 tl =3.0e-2

rtherm.rtherm1 th 6 =5.5e-4
rtherm.rtherm2 6 5 =5.0e-3
rtherm.rtherm3 5 4 =4.5e-2
rtherm.rtherm4 4 3 =10.5e-2
rtherm.rtherm5 3 2 =3.7e-1
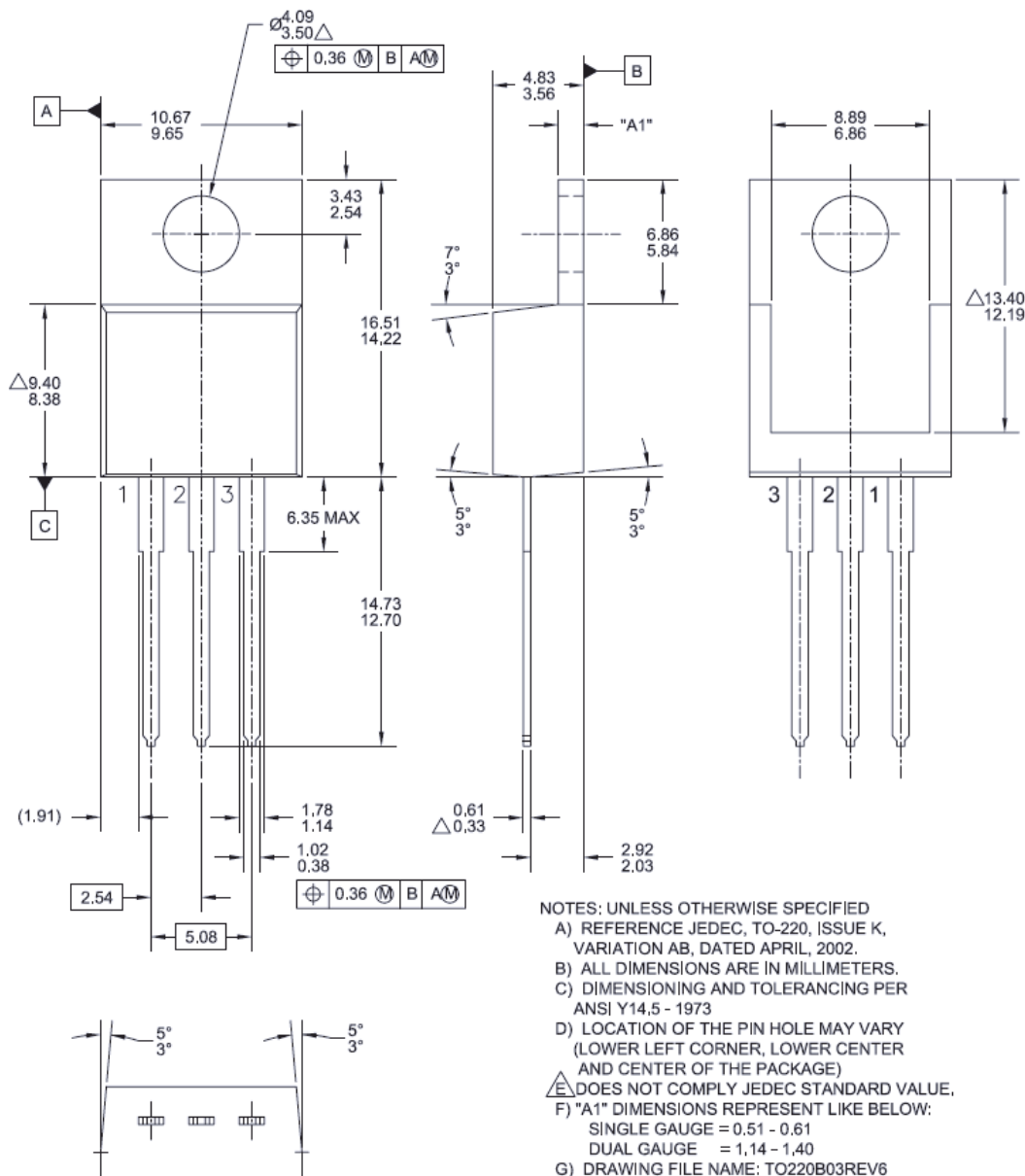rtherm.rtherm6 2 tl =3.8e-1
}

th   JUNCTION

RTHERM1   CTHERM1

6

RTHERM2   CTHERM2

5

RTHERM3   CTHERM3

4

RTHERM4   CTHERM4

3

RTHERM5   CTHERM5

2

RTHERM6   CTHERM6

tl   CASE

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FDP2572 Rev. C1

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Mechanical Dimensions

TO-220 3L

Figure 21. TO-220, Molded, 3Lead, Jedec Variation AB

NOTES: UNLESS OTHERWISE SPECIFIED
A) REFERENCE JEDEC, TO-220, ISSUE K, VARIATION AB, DATED APRIL, 2002.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ANSI Y14,5 - 1973
D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E) DOES NOT COMPLY JEDEC STANDARD VALUE,
F) "A1" DIMENSIONS REPRESENT LIKE BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1,14 - 1,40
G) DRAWING FILE NAME: TO220B03REV6

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-003

Dimension in Millimeters

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BitSiC™
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CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EffcientMax™
ESBC™

Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™

F-PFS™
FRFET®
Global Power Resource℠
GreenBridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Marking Small Speakers Sound Louder
and Better™
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™
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